

4K x 4 CMOS STATIC RAM

- 20, 25, AND 35ns ADDRESS ACCESS TIME
- EQUAL ACCESS AND CYCLE TIMES
- 22-PIN, 300 MIL PLASTIC
- ALL INPUTS AND OUTPUTS TTL COMPATI-BLE, LOW CAPACITANCE, AND PROTECTED AGAINST STATIC DISCHARGE
- TTL STANDBY CURRENT UNAFFECTED BY ADDRESS ACTIVITY
- SEPARATE OUTPUT ENABLE CONTROL
- FLASH CLEAR FUNCTION







PIN NAMES

A ₀ - A ₁₁ - Address	OE - Ouput Enable
DQ ₀ - DQ ₃ - Data I/O	WE - Write Enable
CLR - Flash Clear	GND - Ground
CE - Chip Enable	V _{CC} - + 5V

DESCRIPTION

The MK41H78/79 features fully static operation requiring no external clocks or timing strobes, and equal address access and cycle times. It requires a single + $5V \pm 10$ percent power supply and is fully TTL compatible.

The device has a Chip Enable power down feature which automatically reduces power dissipation when the CE pin is brought inactive (high). Standby power can be further reduced by raising the CE pin to the full V_{CC} voltage. An Output Enable (OE) pin provides a high speed tristate control, allowing fast read/write cycles to be achieved with the common-I/O data bus.

Flash Clear operation is provided on the MK41H79 via the CLR pin, and CE active (low). A low applied to the CLR pin clears all RAM bits to zero, making it especially useful for high speed cache and buffer storage applications.

MK41H78/MK41H79(N,P)-20/25/35

ABSOLUTE MAXIMUM RATINGS*

Parameter	Value	Unit
Voltage on any Pin Relative to GND	- 1.0 to + 7.0	V
Ambient Operating Temperture (T _A)	0 to 70	°C
Ambient Storage Temperature (plastic)	- 55 to + 125	°C
Ambient Storage Temperature (ceramic)	- 65 to +150	°C
Total Device Power Dissipation	1	W
Output Currrent per Pin	50	mA

Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or other conditions beyond those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

TRUTH TABLE

CE	OE	WE	CLR *	Mode	DQ	Power
н	Х	Х	Х	Deselect	High Z	Standby
L	Х	L	н	Write	D _{IN}	Active
L	L	Н	Н	Read	D _{OUT}	Active
L	Н	Н	Н	Read	High Z	Active
L	Х	L	L	Flash Clear	High Z	Active
L	L	Н	L	Flash Clear	Low Z	Active
L	Н	Н	L	Flash Clear	High Z	Active

X = Don't Care

* Applies to MK41H79 only.

RECOMMENDED DC OPERATING CONDITIONS ($0^{\circ}C \le T_{A} \le 70^{\circ}C$)

Symbol	Parameter		Unit	Notes		
Symbol		Min.	Тур.	Max.		Notes
Vcc	Supply Voltage	4.5	5.0	5.5	V	3
GND	Supply Voltage	0	0	0	V	
VIH	Logic 1 Voltage, All Inputs	2.2		V _{CC} + 1 0	V	3
VIL	Logic 0 Voltage, All Inputs	- 0.3		0.8	V	3

DC ELECTRICAL CHARACTERISTICS ($0^{\circ}C \le T_A \le 70^{\circ}C$) ($V_{CC} = 5.0V \pm 10$ percent)

Symbol	Parameter		Unit	Notes		
Symbol	Falameter	Min.	Тур.	Max.	Unit	Notes
I _{CC1}	Average Power Supply Current			120	mA	4
I _{CC2}	TTL Standby Current			16	mA	5
I _{CC3}	CMOS Standby Current			8	mA	6
I _{IL}	Input Leakage Current (any input pin)	- 1		+ 1	μA	7
IOL	Output Leakage Current (any output pin)	- 10		+ 10	μA	8
Voн	Output Logic 1 Voltage (I _{OUT} = - 4 mA)	2.4			V	3
VOL	Output Logic 0 Voltage (I _{OUT} = + 8 mA)			0.4	V	3



CAPACITANCE ($T_A = 25^{\circ}C, f = 1.0MHz$)

Symbol	Parameter		Value				
	Falanielei	Min.	Тур.	Max.		Hotes	
C ₁	Capacitance on Input Pins	4		5	pF	9	
C ₂	Capacitance on DQ Pins	8		10	pF	9	

Notes : 1. Measured with load shown in figure 2(A).

2. Measured with load shown in figure 2(B).

3. All voltages referenced to GND.

4. Icc1 is measured as the average AC current with $V_{CC} = V_{CC}$ (max) and with the outputs open circuit tac = tac (min) is used.

5. CE = VIH, all other inputs = Don't Care.

6. Vcc (max) \geq CE \geq Vcc - 0.3V, all other inputs = Don't Care.

7. Input leakage current specifications are valid for all VIN such that OV < VIN < Vcc. Measured at Vcc = Vcc (max).

8. Output leakage current specifications are valid for all Vout such that OV < Vout < Vcc, CE = VIH and Vcc in valid

AC TEST CONDITIONS

Input Levels	. GND to 3.0V
Transition Times	. 5ns
Input and Output Signal Timing Reference Level	. 1.5V
Ambient Temperature	. 0°C to 70°C
Vcc	$5.0V \pm 10$ percent

Figure 2 : Output Load Circuits.



OPERATIONS

READ MODE

The MK41H78/79 is in the Read Mode whenever WE (Write Enable) is high and CE (Chip Enable) is low, providing a ripple-through access to data from four of 16,384 locations in the static storage array. The unique address specified by the 12 Address Inputs defines which one of 4096 nibbles of data is to be accessed.

Figure 3 : Read-read-read-write Timing.

Valid data will be available at the four Data Output pins within t_{AA} after the last address input signal is stable, providing that the CE and OE (output Enable) access times are satisfied. If CE or OE access times are not met, data access will be measured from the limiting parameter (t_{CEA} or t_{OEA}) rather than the address. The <u>state of the four</u> Data I/O pins is controlled by the CE, WE and OE control signals. The data lines may be in an indeterminate state at t_{CEL} and t_{OEL}, but the data lines will always have valid data at t_{AA}.



AC ELECTRICAL CHARACTERISTICS (read cycle timing) $(0^{\circ}C \le T_A \le 70^{\circ}C)$ (V_{CC} = 5.0V ± 10 percent)

Cumbal	Devenuetan	MK41	H7X-20	MK41H7X-25		MK41H7X-35			
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Notes
^t RC	Read Cycle Time	20		25		35		ns	
t _{AA}	Address Access Time		20		25		35	ns	1
t _{CEL}	Chip Enable to Low-Z	7		7		7		ns	2
t _{CEA}	Chip Enable Access Time		20		25		35	ns	1
toel	Output Enable to Low-Z	2		2		2		ns	2
tOEA	Output Enable Access Time		10		12		15	ns	1
tacs	Read Command Setup Time	0		0		0		ns	
t _{RCH}	Read Command Hold Time	0		0		0		ns	
tон	Valid Data Out Hold Time	5		5		5		ns	1
1 _{CEZ}	Chip Enable to High-Z		8		10		13	ns	2
tOEZ	Output Enable to High-Z		7		8		10	ns	2
1 _{WEZ}	Write Enable to High-Z		8		10		13	ns	2



WRITE MODE

The MK41H78/79 is in the Write Mode whenever the WE and CE inputs are in the low state. CE or WE must be high during address transitions. Addresses must be held valid throughout a write cycle. The Write begins with the concurrence of a low on WE and CE. Therefore, t_{AS} is referenced to the latter oc-



curring edge of CE or WE. The write cycle is terminated by the earlier rising edge of CE or WE.

If the output is enabled (\overline{CE} and \overline{OE} low), then \overline{WE} will return the outputs to high impedance within twez of its falling edge. Care must be taken to avoid bus contention in this type of operation. Data-In must remain valid t_DH after the rising edge of \overline{CE} or \overline{WE} .



AC ELECTRICAL CHARACTERISTICS (write cycle timing) (0°C \leq T_A \leq 70°C) (V_{CC} = 5.0V \pm 10 percent)

		MK41	MK41H7X-20		MK41H7X-25		MK41H7X-35		Neder
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Notes
twc	Write Cycle Time	20		25		35		ns	
tas	Address Setup Time	0		0		0		ns	
taw	Address Stable to End of Write	16		20		30		ns	
L _{AH}	Address Hold after End of Write	0		0		0		ns	
tCEW	Chip Enable to End of Write	18		22		32		ns	
1 _{WEW}	Write Enable to End of Write	16		20		30		ns	
tos	Data Setup Time	12		14		15		ns	
фн	Data Hold Time	0		0		0		ns	
WEL	Write Enable to Low-Z	5		5		5		ns	2

FLASH CLEAR

A Flash Clear cycle sets all 16,384 bits in the RAM to logic zero. A Clear begins at the concurrence of a low on Chip Enable (CE) and Flash Clear (CLR). A Clear may be ended by a high on either CE or CLR. A low on CLR has no effect if the device is dis-

abled (CE high). A Clear may be executed within either a Read or a Write cycle. Figure 4 illustrates a Clear within a Read cycle. Clears within Write cycles are constrained only in that Write timing parameters must be observed as soon as the Flash Clear pin returns high.



Figure 5 : Last Read-flash Clear-first Write (MK41H79 only).

AC ELECTRICAL CHARACTERISTICS (clear cycle timing)

$(0^{\circ}C \leq T_{A})$	≤ 70°C)	$(V_{CC} = 5)$	5.0 ± 10%)
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Question	Parameter	MK41I	MK41H7X-20		MK41H7X-25		MK41H7X-35		
Symbol		Min.	Max.	Min.	Max.	Min.	Max.	Unit	Notes
1+cc	Flash Clear Cycle Time	40		50		70		ns	
^t CEC	Chip Enable Low to End of Clear	40		50		70		ns	
T _{CLP}	Flash Clear Low to End of Clear	38		48		68		ns	
t _{CX}	Clear to Inputs Don't Care	0		0		0		ns	
t _{CR}	End of Clear to Inputs Recognized	0		0		0		ns	
^t cwx	Clear to Write Enable Don't Care	0		0		0		ns	
tонс	Valid Data Out Hold from Clear	5		5		5		ns	1



STANDBY MODE

The MK41H78/79 is in Standby Mode whenever \overline{CE} is held at or above $V_{\text{IH}}.$

Figure 6 : Standby Mode.



AC ELECTRICAL CHARACTERISTICS (standby mode) $(0^{\circ}C \le T_{A} \le 70^{\circ}C)$ (V_{CC} = 5.0V ± 10 percent)

Symbol	Parameter	MK41H7X-20		MK41H7X-25		MK41H7X-35		11-14	
		Min.	Max.	Min.	Max.	Min.	Max.	Unit	Notes
teo	Chip Enable High to Power Down		20		25		35	ns	
leu	Chip Enable Low to Power up	0		0		0		ns	

APPLICATION

The MK41H78/79 operates from a 5.0 volt supply. It is compatible with all standard TTL families on all inputs and outputs. The device should share a solid ground plane with any other devices interfaced with it, particularly TTL devices. Additionally, because the outputs can drive rail-to-rail into high impedance loads, the 41H79 can also interface to 5 volt CMOS on all inputs and outputs. Refer to the normalized performance curves that follow.

Since very high frequency current transients will be associated with the operation of the MK41H79, power line inductance must be minimized on the circuit board power distribution network. Power and ground tracegridding or separate power planes can be employed to reduce line inductance. Additionally, a high frequency decoupling capacitor should be placed next to each RAM. The capacitor should be $0.1\mu F$ or larger. A pull-up resistor is also recommended for CLR on the MK41H79. This will ensure that any low going system noise, coupled onto the input, does not drive CLR below V_{IH} minimum specifications.

Though often times not thought of as such, the traces on a memory board are basically unterminated, low impedance transmission lines. As such they are subject to signal reflections manifested as noise, undershoots and excessive ringing. Series termination in close proximity to the TTL drivers can improve driver/signal path impedance matching. While experimentation most often proves to be the only practical approach to selection of series resistors, values in the range of 10 to 33 Ω often prove most suitable.



NORMALIZED DC AND AC PERFORMANCE CHARACTERISTICS









1.18 1 16 NORMALIZED SUPPLY CURRENT VS.

AMBIENT TEMPERATURE Voc = 5.0V

120









NORMALIZED ACCESS TIME VS. OUTPUT LOADING V CC = 5.0V TA = 25 °C



SGS-THOMSON

MICROELECTROMICS

NORMALIZED DC AND AC PERFORMANCE CHARACTERISTICS



NORMALIZED SOURCE AND SINK CURRENTS VS. OUTPUT VOLTAGE V ... = 5.0V T .= 25°C











NORMALIZED SOURCE AND SINK CURRENTS VS. SUPPLY VOLTAGE T, =25 °C



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ORDER CODES

Part Number	Access Time	Package Type	Temperature Range
MK41H78N-20	20ns	22 Pin Plastic DIP	0°C to 70°C
MK41H78N-25	25ns	22 Pin Plastic DIP	0°C to 70°C
MK41H78N-35	35ns	22 Pin Plastic DIP	0°C to 70°C
MK41H79N-20	20ns	22 Pin Plastic DIP	0°C to 70°C
MK41H79N-25	25ns	22 Pin Plastic DIP	0°C to 70°C
MK41H79N-35	35ns	22 Pin Plastic DIP	0°C to 70°C



PACKAGE DESCRIPTION



Notes: 1. Overall length includes 010 in flash on either end of the package 2. Package standoff to be measured per jedec requirements.

3. The maximum limit shall be increased by 003 in when solder lead finish is specified

